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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet of 3

Complete if Known					
Application Number 10/614,067 (Conf. No. 8117)					
Filing Date	July 3, 2003				
First Named Inventor Leedy					
Art Unit	2822				
Examiner Name	Pamela Perkins				
Attorney Docket Number	ELM-2 Div. 6				

Examiner Cit		Document Number	Publication Date	Name of Patentee or	Pages, Columns, Lines, Wher Relevant Passages or Relevant	
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Examiner Signature	/Pamela Perkins/	Date Considered	05/08/2006

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Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number. Complete if Known Substitute for form 1449A/B/PTO 10/614,067 (Conf. No. 8117) Application Number **INFORMATION DISCLOSURE** July 3, 2003 Filing Date STATEMENT BY APPLICANT First Named Inventor Leedy 2822 Art Unit (Use as many sheets as necessary) Pamela Perkins Examiner Name Attorney Docket Number ELM-2 Div. 6 2 of 3 Sheet

<u> </u>	FOREIGN PATENT DOCUMENTS									
Superiors.		Cita	Cito	Cita	T	Foreign Patent Document	Publication Date	Name of Patentee or	Pages, Columns, Lines, Where Relevant Passages	
	Examiner Cite Initials* No.1	No.1	Country Code ³ -Number ⁴ -Kind Code ⁵ (If known)	MM-DD-YYYY	Applicant of Cited Document	or Relevant Figures Appear				
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Examiner Initials	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²		
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Examiner	/Pamela Perkins/	Date	05/08/2006
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		NON PATENT LITERATURE DOCUMENTS					
Examiner Initials	er Cite No. Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), public and/or country where published.						
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^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹Applicant's unique citation designation number (optional). ²See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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